

LMK00804B-Q1 1.5V 至 3.3V、1 路至 4 路高性能 LVCMOS 扇出缓冲器和电平转换器

1 特性

- 下列性能符合 AEC-Q100 标准：
 - 器件温度等级 1: -40°C 至 $+125^{\circ}\text{C}$, T_A
- 支持 1.5V 至 3.3V 电平范围的四路 LVCMOS/LVTTL 输出
 - 附加抖动: 在 40MHz 时为 0.1ps RMS (典型值)
 - 本底噪声: 在 40MHz 时为 -168dBc/Hz (典型值)
 - 输出频率: 350MHz (最大值)
 - 输出偏斜: 35ps (最大值)
 - 器件间偏移: 550ps (最大值)
- 两个可选输入
 - CLK_P、CLK_N 组合可接受 LVPECL、LVDS、HCSL、SSTL、LVHSTL 或 LVCMOS/LVTTL
 - LVCMOS_CLK 可接受 LVCMOS/LVTTL
- 同步时钟使能端
- 核心/输出电源:
 - 3.3V/3.3V
 - 3.3V/2.5V
 - 3.3V/1.8V
 - 3.3V/1.5V

- 封装: 16 引脚 VQFN

2 应用

- 高级驾驶辅助系统 (ADAS)
 - 前向式远距离雷达
 - 中等/短距离雷达
 - 超短距离雷达

3 说明

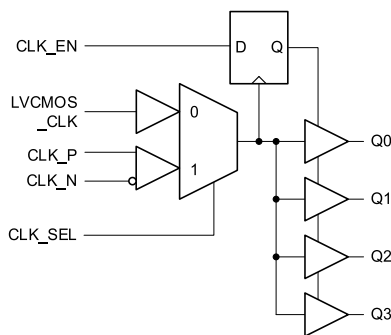
LMK00804B-Q1 是一款高性能时钟扇出缓冲器和电平转换器，通过可接受差动或单端输入的两个可选输入之一提供最多四种 LVCMOS/LVTTL 输出 (3.3V、2.5V、1.8V 或 1.5V 电平)。时钟使能输入在内部同步，以便在时钟使能端子被置为有效或无效时，消除输出上的欠幅脉冲或毛刺脉冲。禁用时钟后，输出将保持逻辑低电平状态。LMK00804B-Q1 也能在四个收发器之间分配低抖动时钟，并提高级联毫米波雷达系统中的总体目标检测率和分辨率。

器件信息(1)

器件型号	封装	封装尺寸 (标称值)
LMK00804B-Q1	VQFN (16)	3.00mm × 3.00mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

简化原理图



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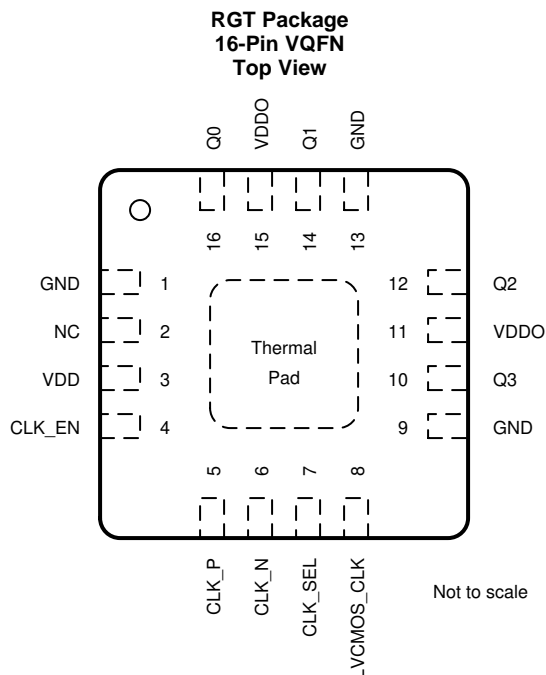
4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision A (June 2019) to Revision B	Page
• 将器件间偏移最大值从 700ps 更改为 550ps	1
• 将前置远距离雷达应用更改为前向式远距离雷达	1
• 更改了简化原理图 图示	1
• Changed pin 2 in the RGT package from: OE to: NC	3
• Changed the pin descriptions	3
• Changed Changed CDM ESD ratings from: +/-250 V to: +/-750 V	4
• Added the <i>Typical Characteristics</i> section back to the data sheet	8
• Changed <i>Differential Input Level</i> timing diagram	9
• Changed the <i>Overview</i> section	10
• Changed <i>Functional Block Diagram</i>	10
• Added the <i>Typical Connection Diagram</i>	12
• Changed the <i>Power Considerations</i> section to <i>Power Dissipation Calculations</i>	16
• Moved the <i>Thermal Management</i> section to <i>Do's and Don'ts</i>	16
• Changed the recommendations for unused output pins	17
• Changed the <i>Input Slew Rate Considerations</i> section	17
• Added content to the <i>Ground Planes</i> section	18
• Changed the <i>Layout Example</i> section	19

Changes from Original (March 2019) to Revision A	Page
• 将数据表状态从“预告信息”更改为“生产数据”	1

5 Pin Configuration and Functions



Pin Functions⁽¹⁾

PIN		TYPE ⁽²⁾	DESCRIPTION
NAME	NO.		
CLK_EN	4	I, PU	Synchronous clock enable input. CLK_EN must be held low until a valid reference clock is provided. Typically connected to VDD with an external 1-k Ω pullup. When unused, leave floating. 0 = Outputs are forced to logic low state 1 = Outputs are enabled with LVCMOS/LVTTL levels
CLK_N	6	I, PD, PU	Inverting differential clock input with internal 51-k Ω (typ) pullup resistor to VDD and internal 51-k Ω (typ) pulldown resistor to GND. Typically connected to the inverting clock input. When unused, leave floating. Internally biased to $V_{DD}/2$ when left floating.
CLK_P	5	I, PD	Noninverting differential clock input with internal 51-k Ω (typ) pulldown resistor to GND. Typically connected to the noninverting clock input. A single-ended clock input can also be connected to CLK_P. When unused, leave floating.
CLK_SEL	7	I, PU	Clock select input. Typically connected to VDD with an external 1-k Ω pullup. When unused, leave floating. 0 = Select LVCMOS_CLK (pin 8) 1 = Select CLK_P, CLK_N (pins 5, 6)
GND	1, 9, 13	G	Power supply ground.
LVCMOS_CLK	8	I, PD	Single-ended clock input with internal 51-k Ω (typ) pulldown resistor to GND. Typically connected to a single-ended clock input. When unused, leave floating. Accepts LVCMOS/LVTTL levels.
NC	2	NC	No connect pin. Typically left floating. Do not connect to GND.
Q0	16	O	Single-ended clock outputs with LVCMOS/LVTTL levels at 7- Ω output impedance. Typically connected to a receiver with a 43- Ω series termination. When unused, leave floating.
Q1	14		
Q2	12		
Q3	10		

(1) See [Recommendations for Unused Input and Output Pins](#), if applicable.

(2) G = Ground, I = Input, O = Output, P = Power, PU = 51-k Ω pullup, PD = 51-k Ω pulldown. NC = No connect

Pin Functions⁽¹⁾ (continued)

PIN		TYPE ⁽²⁾	DESCRIPTION
NAME	NO.		
VDD	3	P	Power supply terminal. Typically connected to a 3.3-V supply. The VDD pin is typically connected GND with an external 0.1-uF capacitor.
VDDO	11, 15	P	Output supply terminals. Typically connected to a 3.3-V, 2.5-V, 1.8-V, or 1.5-V supply. The VDDO pins are typically connected GND with external 0.1-uF capacitors.

6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾⁽²⁾

Over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{DD}	Supply input voltage		-0.3	3.6	V
V _{DDO}	Supply output voltage		-0.3	3.6	V
V _I	Input voltage	CLK_EN, CLK_SEL, CLK_P, CLK_N, LVCMOS_CLK	-0.3	V _{DD} + 0.3	V
	Input voltage	Q0, Q1, Q2, Q3	-0.3	V _{DDO} + 0.3	V
T _J	Junction temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) If Military/Aerospace specified devices are required, contact the Texas Instruments Sales Office/Distributors for availability and specifications.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾ HBM ESD Classification Level 2	±2000	V
		Charged-device model (CDM), per AEC Q100-011 CDM ESD Classification Level C5	±750	

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V _{DD}	Supply input voltage		3.135	3.3	3.465	V
V _{DDO}	Supply output voltage		3.135	3.3	3.465	V
			2.375	2.5	2.625	
			1.71	1.8	1.89	
			1.425	1.5	1.575	
T _A	Ambient temperature		-40		125	°C
T _J	Junction temperature		-40		135	°C
f _{OUT}	Maximum output frequency ⁽¹⁾				350	MHz

- (1) There is no minimum input / output frequency provided the input slew rate is sufficiently fast. Refer to *Input Slew Rate Considerations*.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾⁽²⁾		LMK00804B-Q1	UNIT
		RGT (VQFN)	
		16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	48.0	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	58.6	°C/W
R _{θJB}	Junction-to-board thermal resistance	22.6	°C/W
ψ _{JT}	Junction-to-top characterization parameter	2.1	°C/W
ψ _{JB}	Junction-to-board characterization parameter	22.6	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	6.5	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report (SPRA953).
- (2) The package thermal impedance is calculated in accordance with JESD 51 and JEDEC2S2P (high-K board).

6.5 Power Supply Characteristics

Over recommended operating supply and temperature ranges unless otherwise specified.

PARAMETER		MIN	TYP	MAX	UNIT
I _{DD}	Power supply current through VDD			21	mA
I _{DDO}	Power supply current through VDDO			5	mA

6.6 LVC MOS / LV TTL DC Electrical Characteristics

 $V_{DD} = 3.3\text{ V} \pm 5\%$, $V_{DDO} = 1.5\text{ V} \pm 5\%$, $1.8\text{ V} \pm 5\%$, $2.5\text{ V} \pm 5\%$, $3.3\text{ V} \pm 5\%$ and $T_A = -40^\circ\text{C}$ to 125°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{IH}	Input high voltage	CLK_EN, CLK_SEL		2		$V_{DD} + 0.3$	V
		LVC MOS_CLK		2		$V_{DD} + 0.3$	V
V_{IL}	Input low voltage	CLK_EN, CLK_SEL		-0.3		0.8	V
		LVC MOS_CLK		-0.3		1.3	V
I_{IH}	Input high current	CLK_EN, CLK_SEL	$V_{IH} = V_{DD}$			15	μA
		LVC MOS_CLK	$V_{DD} = 3.465\text{ V}$, $V_{IN} = 3.465\text{ V}$			150	
I_{IL}	Input low current	CLK_EN, CLK_SEL	$V_{IL} = \text{GND}$	-150			μA
		LVC MOS_CLK	$V_{DD} = 3.465\text{ V}$, $V_{IN} = 0\text{ V}$	-150			
V_{OH}	Output high voltage ⁽¹⁾	$V_{DDO} = 3.3\text{ V} \pm 5\%$		2.64			V
		$V_{DDO} = 2.5\text{ V} \pm 5\%$		2			
		$V_{DDO} = 1.8\text{ V} \pm 5\%$		1.44			
		$V_{DDO} = 1.5\text{ V} \pm 5\%$		1.2			
V_{OL}	Output low voltage ⁽¹⁾	$V_{DDO} = 3.3\text{ V} \pm 5\%$				0.66	V
		$V_{DDO} = 2.5\text{ V} \pm 5\%$				0.5	
		$V_{DDO} = 1.8\text{ V} \pm 5\%$				0.36	
		$V_{DDO} = 1.5\text{ V} \pm 5\%$				0.3	
I_{OZL}	Output Hi-Z current low			-5			μA
I_{OZH}	Output Hi-Z current high					5	

(1) Outputs terminated with $50\ \Omega$ to $V_{DDO}/2$.

6.7 Differential Input DC Electrical Characteristics

 $V_{DD} = 3.3\text{ V} \pm 5\%$, $V_{DDO} = 1.5\text{ V} \pm 5\%$, $1.8\text{ V} \pm 5\%$, $2.5\text{ V} \pm 5\%$, $3.3\text{ V} \pm 5\%$ and $T_A = -40^\circ\text{C}$ to 125°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{ID}	Differential input voltage swing, $(V_{IH} - V_{IL})^{(1)}$			0.15		1.4	V
V_{IC}	Input common-mode voltage ⁽¹⁾⁽²⁾			0.5		$V_{DD} - 0.85$	V
I_{IH}	Input high current ⁽³⁾	CLK_N, CLK_P	$V_{DD} = 3.465\text{ V}$, $V_{IN} = 3.465\text{ V}$			150	μA
I_{IL}	Input low current ⁽³⁾	CLK_N, CLK_P	$V_{DD} = 3.465\text{ V}$, $V_{IN} = 0\text{ V}$	-150			μA

(1) V_{IL} should not be less than -0.3 V .

(2) Input common-mode voltage is defined as V_{IH} .

(3) For I_{IH} and I_{IL} measurements on CLK_P or CLK_N, one must comply with V_{ID} and V_{IC} specifications by using the appropriate bias on CLK_N or CLK.

6.8 Switching Characteristics

 $V_{DD} = 3.3\text{ V} \pm 5\%$, $V_{DDO} = 1.5\text{ V} \pm 5\%$, $1.8\text{ V} \pm 5\%$, $2.5\text{ V} \pm 5\%$, $3.3\text{ V} \pm 5\%$ and $T_A = -40^\circ\text{C}$ to 125°C

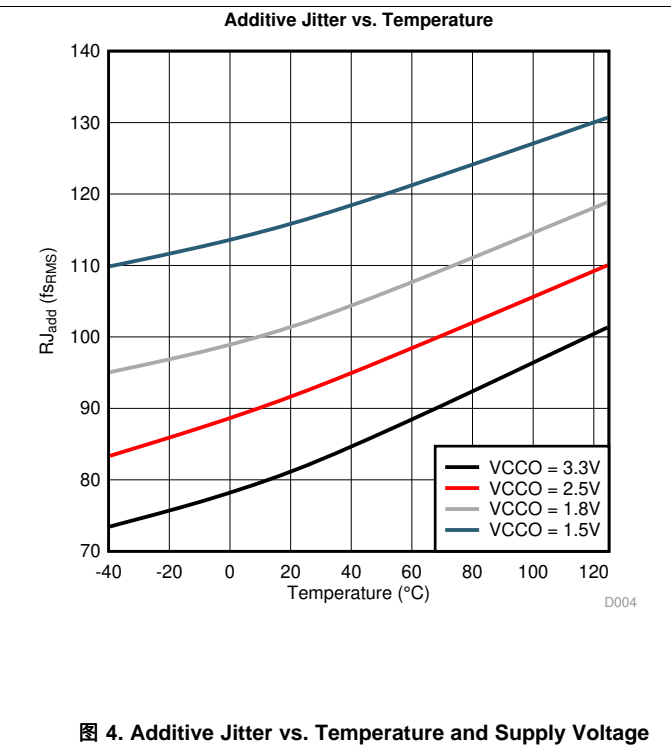
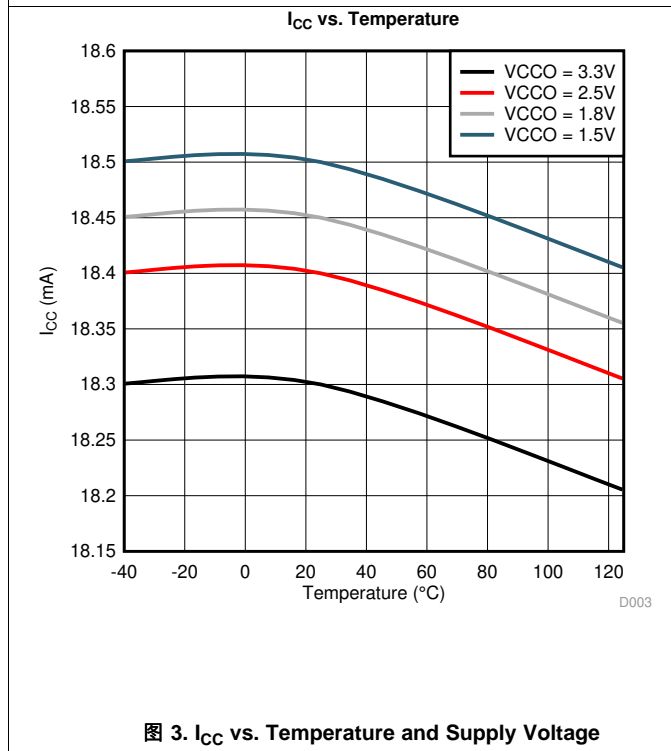
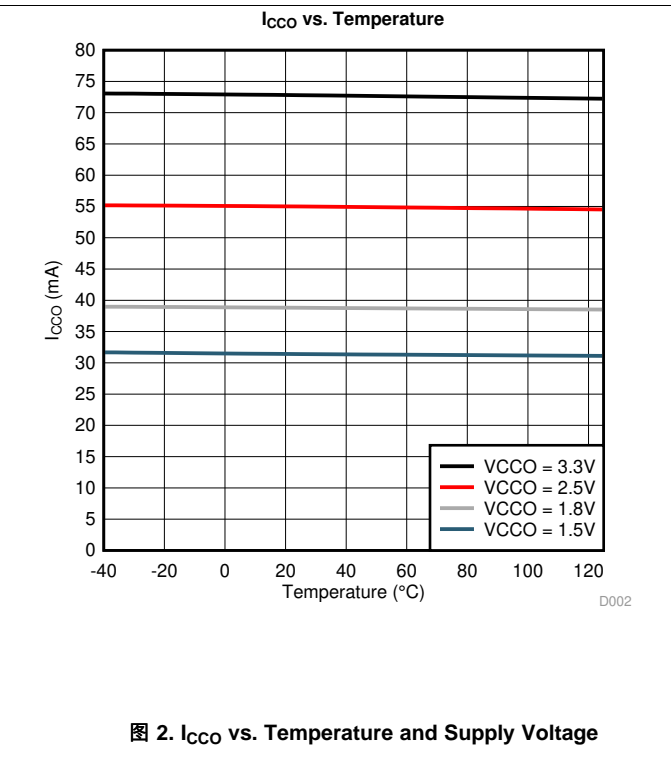
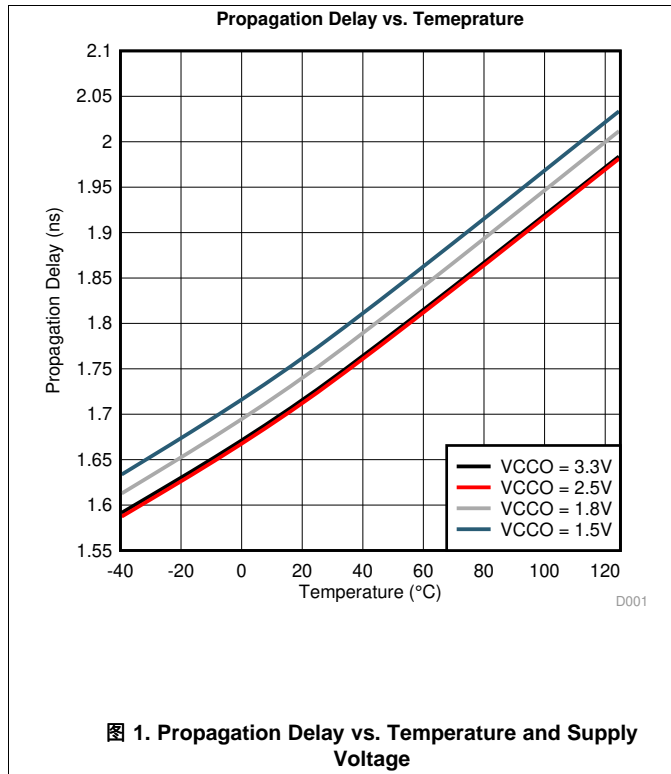
PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t_{PDLH}	Propagation delay, Low-to-high	LVC MOS_CLK ⁽¹⁾ , CLK_P/CLK_N ⁽²⁾	-40°C to 125°C	1		2.5	ns
$t_{SK(O)}$	Output skew ⁽³⁾⁽⁴⁾	Measured on rising edge				35	ps
$t_{SK(PP)}$	Part-to-part skew ⁽⁴⁾⁽⁵⁾					550	ps
t_R/t_F	Output rise/fall time	20% to 80%, $C_L = 5\text{ pF}$		100	310	600	ps
t_{JIT}	Additive jitter ⁽⁶⁾	f = 40 MHz, Input slew rate = 1.25 V/ns, 12-kHz to 20-MHz integration band			115	200	fs RMS
PN_{FLOOR}	Phase noise floor ⁽⁷⁾	f = 40 MHz, Input slew rate = 1.25 V/ns	10-kHz offset		-151		dBc/Hz
			100-kHz offset		-160		
			1-MHz offset		-162		
			10-MHz offset		-162		
			20-MHz offset		-162		
D_O	Output duty cycle	REF = CLK_P/CLK_N, 50% input duty cycle, f < 166 MHz		45%		55%	
		REF = LVC MOS_CLK, 50% input duty cycle, f > 166 MHz		42%		58%	

- (1) Measured from the $V_{DD}/2$ of the input to the $V_{DDO}/2$ of the output.
- (2) Measured from the differential input crossing point to $V_{DDO}/2$ of the output.
- (3) Defined as skew between outputs at the same supply voltage and with equal loading conditions. Measured at $V_{DDO}/2$ of the output.
- (4) Parameter is defined in accordance with JEDEC Standard 65.
- (5) Calculation for part-to-part skew is the difference between the fastest and slowest t_{PD} across multiple devices, various supply voltages, operating at the same frequency, same temperature, with equal load conditions, and using the same type of inputs on each device.
- (6) Buffer additive jitter: $t_{JIT} = \text{SQRT}(t_{JIT_SYS}^2 - t_{JIT_SOURCE}^2)$, where t_{JIT_SYS} is the RMS jitter of the system output (source+buffer) and t_{JIT_SOURCE} is the RMS jitter of the input source, and system output noise is not correlated to the input source noise. Additive jitter should be considered only when the input source noise floor is 3 dB or better than the buffer noise floor (PN_{FLOOR}). This is usually the case for high-quality, ultra-low-noise oscillators. Refer to [System-Level Phase Noise and Additive Jitter Measurement](#) for input source and measurement details.
- (7) Buffer phase noise floor: $PN_{FLOOR} (\text{dBc/Hz}) = 10 \times \log_{10}[10^{(PN_{SYSTEM}/10)} - 10^{(PN_{SOURCE}/10)}]$, where PN_{SYSTEM} is the phase noise floor of the system output (source+buffer) and PN_{SOURCE} is the phase noise floor of the input source. Buffer Phase Noise Floor should be considered only when the input source noise floor is 3 dB or better than the buffer noise floor (PN_{FLOOR}). This is usually the case for high-quality, ultra-low-noise oscillators. Refer to [System-Level Phase Noise and Additive Jitter Measurement](#) for input source and measurement details.

6.9 Pin Characteristics

		MIN	TYP	MAX	UNIT
C_I	Input capacitance		1		pF
R_{PU}	Input pullup resistance		51		k Ω
R_{PD}	Input pulldown resistance		51		k Ω
C_{PD}	Power dissipation capacitance (per output)		2		pF
R_{OUT}	Output impedance		7		Ω

6.10 Typical Characteristics



7 Parameter Measurement Information

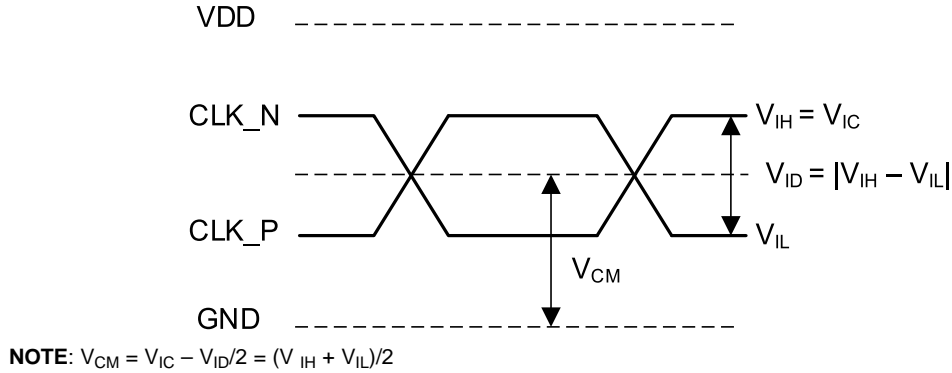


图 5. Differential Input Level

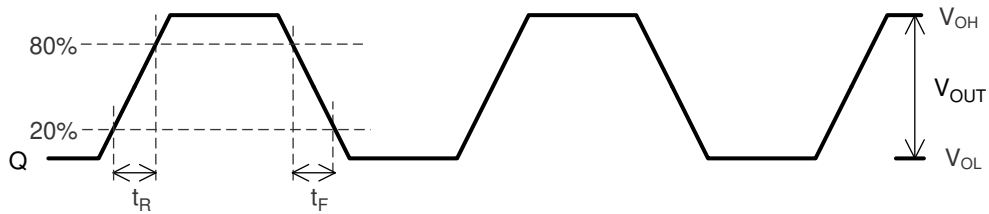


图 6. Output Voltage, and Rise and Fall Times

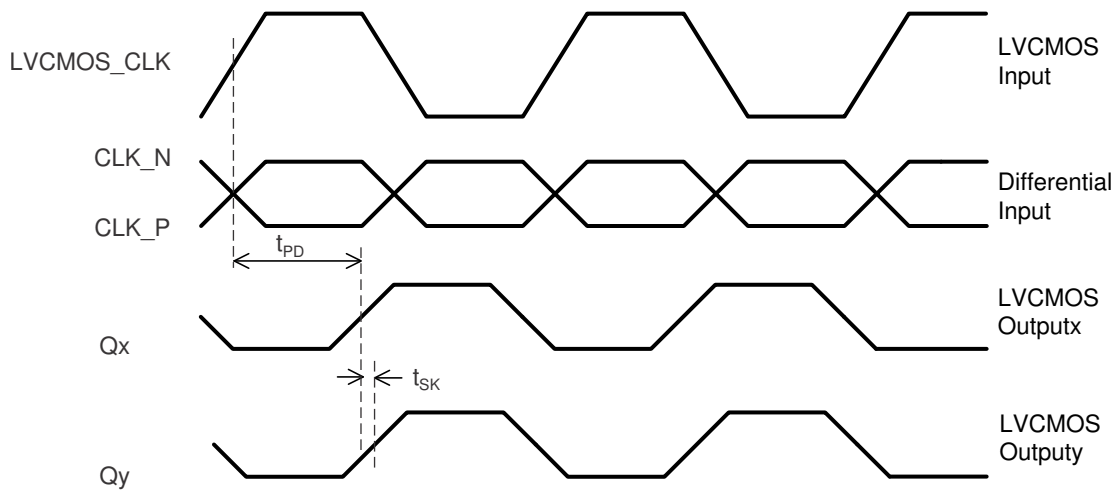


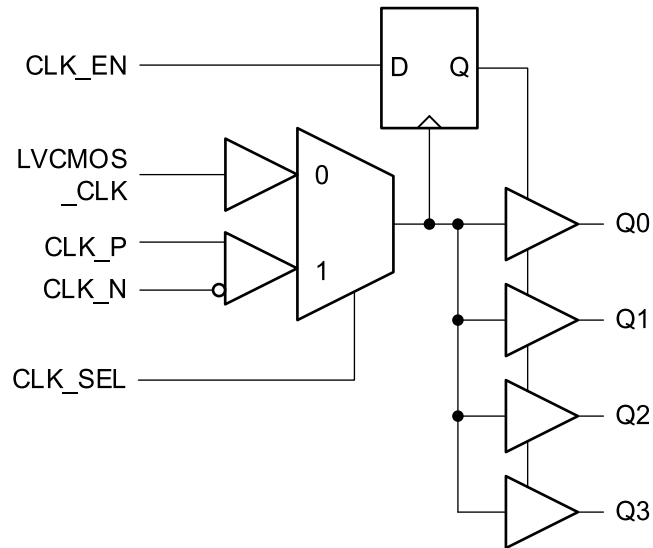
图 7. Output Skew and Propagation Delay

8 Detailed Description

8.1 Overview

The LMK00804B-Q1 is a clock fan-out buffer with two selectable clock inputs and four LVCMOS outputs. The LVCMOS_CLK input accepts a single-ended clock input, and the CLK_P/CLK_N input accepts a differential or single-ended clock input. The LMK00804B-Q1 has a synchronous clock enable feature that allows the device to synchronously enable or disable the outputs using the CLK_EN pin.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Clock Enable Timing

After CLK_EN switches, the clock outputs are disabled or enabled following a rising and falling input clock edge as shown in 图 8.

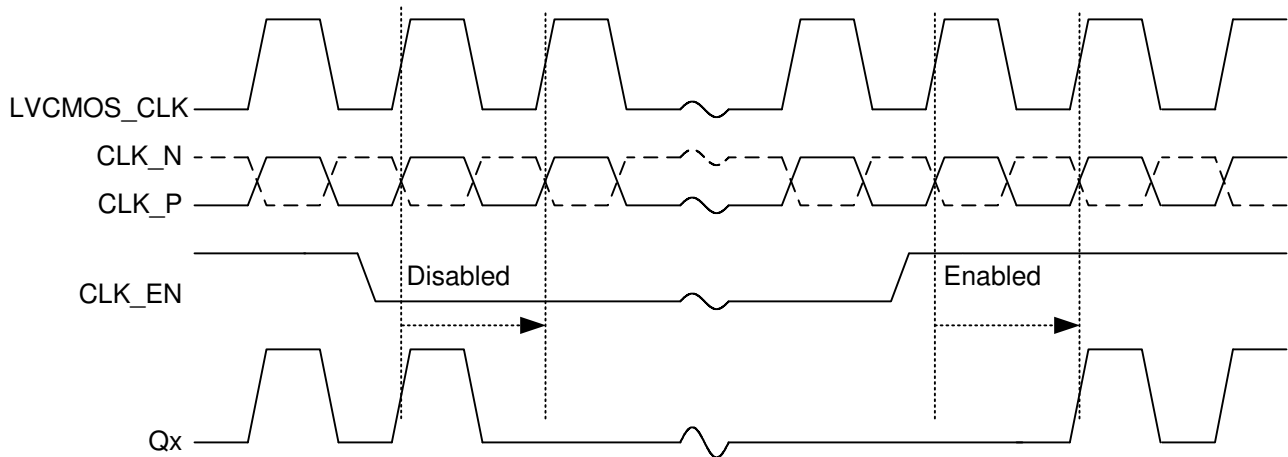


图 8. Clock Enable Timing Diagram

8.4 Device Functional Modes

The device can provide fan-out and level translation from a differential or single-ended input to a LVCMOS/LVTTL output where the output V_{OH} and V_{OL} levels are applied to the V_{DDO} pin and output load condition.

9 Applications and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The LMK00804B-Q1 enables the distribution of up to four LVCMOS copies of a low-noise source designed for general-purpose and high-performance applications. For best jitter performance, TI recommends to use the appropriate matching networks for the clock driver and receiver format, as detailed in the *Typical Applications* section. Practice good high-speed layout design outlined in the *High-speed Layout Guidelines* application report (SCAA082).

The LMK00804B-Q1 is designed to drive 50-Ω controlled-impedance traces. TI recommends to design these clock traces as 50-Ω, single-ended controlled impedance traces. Use a series 43-Ω resistor at the clock outputs Q[3:0] to match the driver impedance and series resistance to the trace impedance.

9.2 Typical Applications

Refer to the following sections for output clock and input clock interface circuits.

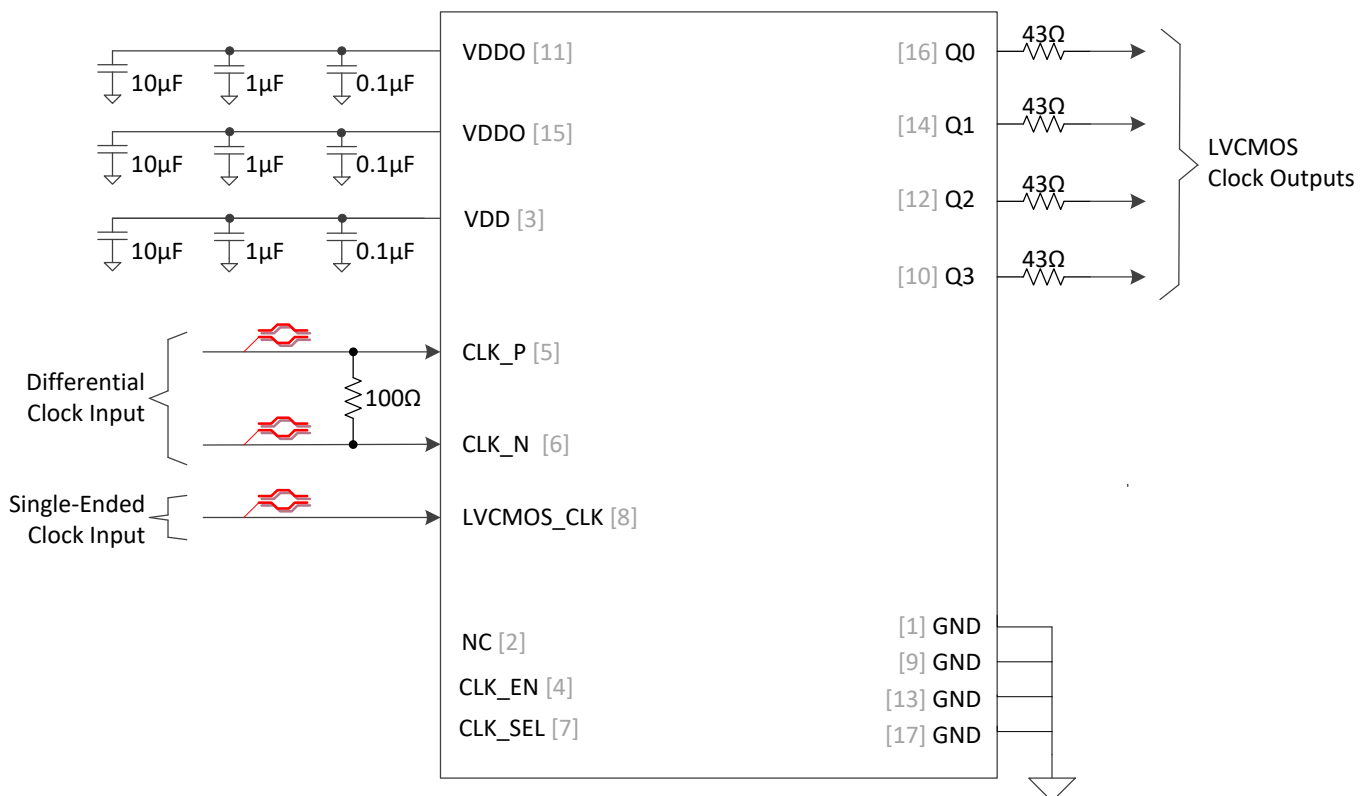


图 9. Typical Connection Diagram

Typical Applications (接下页)

9.2.1 Output Clock Interface Circuit

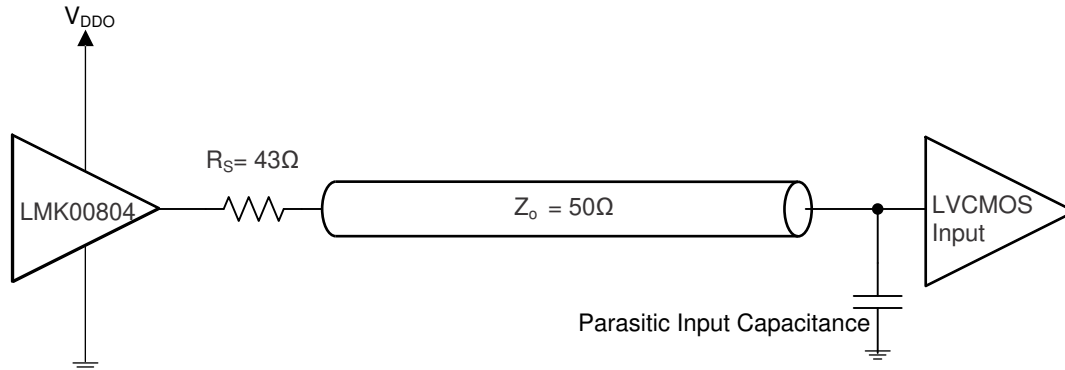


图 10. LVC MOS Output Configuration

9.2.1.1 Design Requirements

For high-performance devices, limitations of the equipment can affect phase-noise measurements. The noise floor of the equipment is often higher than the noise floor of the device. The real noise floor of the device is probably lower. It is important to understand that system-level phase noise measured at the DUT output is influenced by the input source and the measurement equipment.

For 图 11 and system-level phase noise plots, a Rohde & Schwarz SMA100A low-noise signal generator was cascaded with an Agilent 70429A K95 single-ended-to-differential converter block with ultra-low phase noise and fast-edge slew rate (>3 V/ns) to provide a low-noise clock input source to the LMK00804B-Q1. An Agilent E5052 source signal analyzer with an ultra-low measurement noise floor was used to measure the phase noise of the input source (SMA100A + 70429A K95) and system output (input source + LMK00804B-Q1). The light blue trace shows the input source phase noise, and the dark blue trace in 图 11 shows the system output phase noise.

Typical Applications (接下页)

9.2.1.2 Detailed Design Procedure

Use 公式 1 to calculate the additive phase noise or noise floor of the buffer (PN_{FLOOR}):

$$PN_{FLOOR} \text{ (dBc/Hz)} = 10 \times \log_{10}[10^{(PN_{SYSTEM}/10)} - 10^{(PN_{SOURCE}/10)}]$$

where

- PN_{SYSTEM} is the phase noise of the system output (source+buffer)
 - PN_{SOURCE} is the phase noise of the input source
- (1)

Use 公式 2 to calculate the additive jitter of the buffer (t_{JIT}):

$$t_{JIT} = \text{SQRT}(t_{JIT_SYS}^2 - t_{JIT_SOURCE}^2)$$

where:

- t_{JIT_SYS} is the RMS jitter of the system output (source+buffer), integrated from 10 kHz to 20 MHz
 - t_{JIT_SOURCE} is the RMS jitter of the input source, integrated from 10 kHz to 20 MHz
- (2)

9.2.1.3 Application Curve

9.2.1.3.1 System-Level Phase Noise and Additive Jitter Measurement

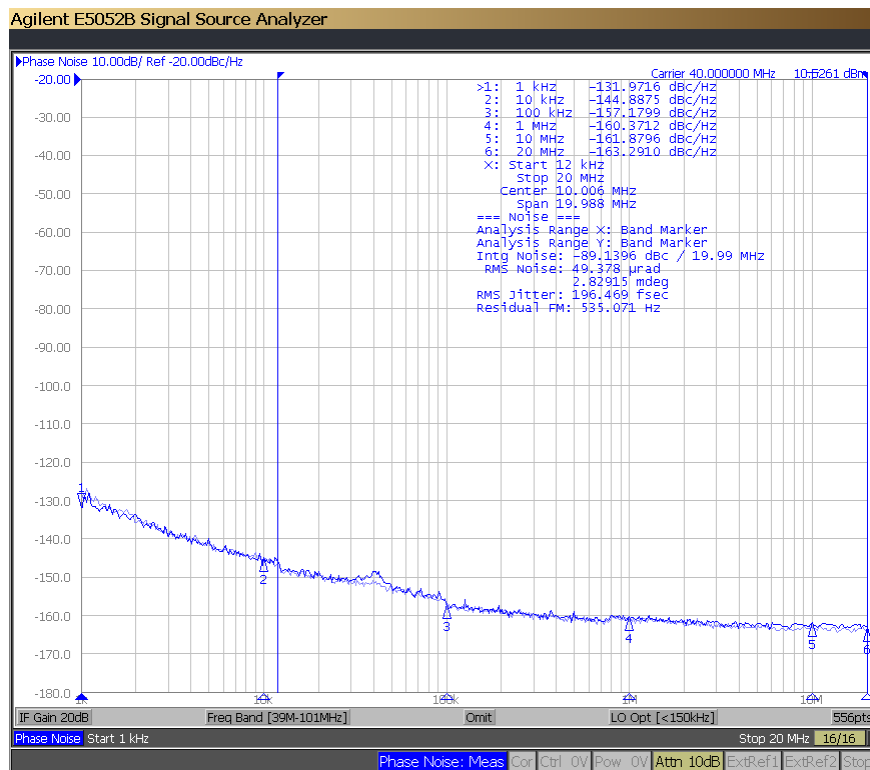


图 11. 40-MHz Input Phase Noise (181 fs rms, Light Blue), and Output Phase Noise (196 fs rms, Dark Blue), Additive Jitter = 77 fs rms

Typical Applications (接下页)

9.2.2 Input Detail

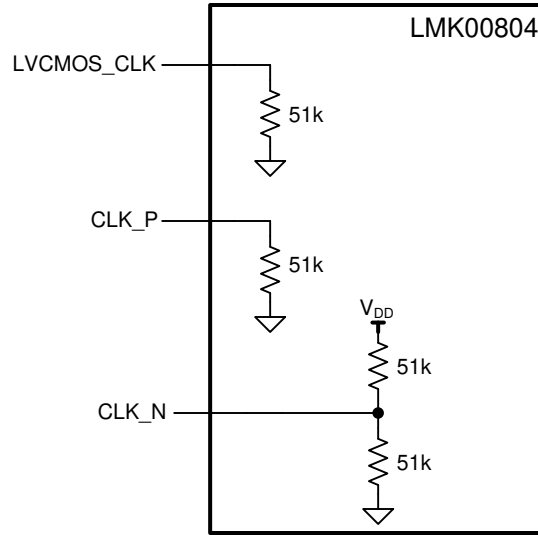


图 12. Clock Input Components

9.2.3 Input Clock Interface Circuits

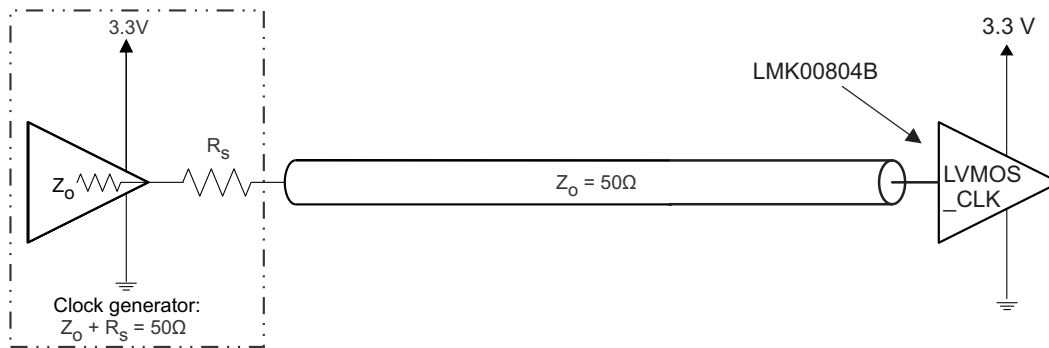
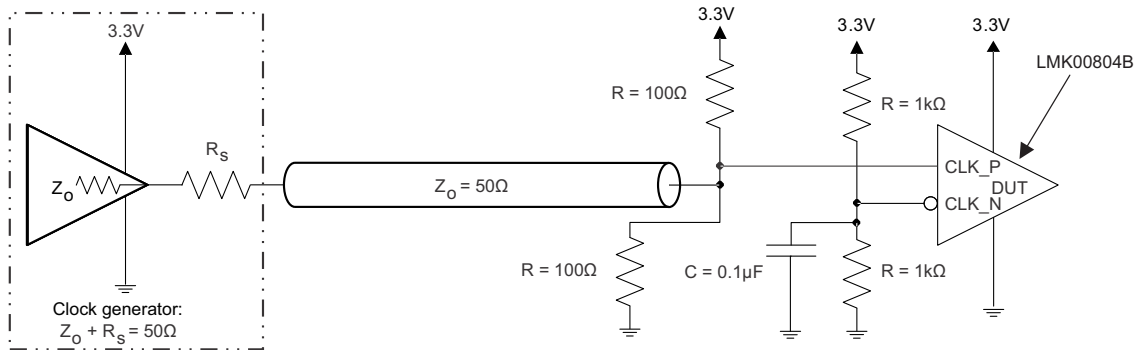


图 13. LVC MOS_CLK Input Configuration



- (1) The Thevenin/split termination values ($R = 100\ \Omega$) at the CLK_P input may be adjusted to provide a small differential offset voltage (50 mV, for example) between the CLK_P and CLK_N inputs to prevent input chatter if the LVC MOS driver in a tri-state condition. For example, the engineer can use $105\ \Omega$ 1% to the 3.3-V rail and $97.6\ \Omega$ 1% to GND to receive a -60-mV offset voltage ($V_{CLK_N} - V_{CLK_P}$). Ensure a logic low state if the LVC MOS driver enters a tri-state condition.

图 14. Single-Ended/LVC MOS Input DC Configuration

9.3 Do's and Don'ts

9.3.1 Power Dissipation Calculations

The following power considerations refer to the device-consumed power consumption only. The device power consumption is the sum of static and dynamic power. The dynamic power usage consists of two components:

- Power used by the device as it switches states
- Power required to charge any output load

The output load can be capacitive-only or capacitive and resistive. Use [公式 3](#) through [公式 5](#) to calculate the power consumption of the device:

$$P_{Dev} = P_{stat} + P_{dyn} + P_{Cload} \quad (3)$$

$$P_{stat} = (I_{DD} \times V_{DD}) + (I_{DDO} \times V_{DDO}) \quad (4)$$

$$P_{dyn} + P_{Cload} = (I_{DDO,dyn} + I_{DDO,Cload}) \times V_{DDO}$$

where:

- $I_{DDO,dyn} = C_{PD} \times V_{DDO} \times f \times n$ [mA]
 - $I_{DDO,Cload} = C_{load} \times V_{DDO} \times f \times n$ [mA]
- (5)

Example for power consumption of the LMK00804B-Q1: 4 outputs are switching, $f = 100$ MHz,

$V_{DD} = V_{DDO} = 3.465$ V and assuming $C_{load} = 5$ pF per output:

$$P_{Dev} = 90 \text{ mW} + 34 \text{ mW} = 124 \text{ mW} \quad (6)$$

$$P_{stat} = (21 \text{ mA} \times 3.465 \text{ V}) + (5 \text{ mA} \times 3.465 \text{ V}) = 90 \text{ mW} \quad (7)$$

$$P_{dyn} + P_{Cload} = (2.8 \text{ mA} + 6.9 \text{ mA}) \times 3.465 \text{ V} = 34 \text{ mW} \quad (8)$$

$$I_{DD,dyn} = 2 \text{ pF} \times 3.465 \text{ V} \times 100 \text{ MHz} \times 4 = 2.8 \text{ mA} \quad (9)$$

$$I_{DD,Cload} = 5 \text{ pF} \times 3.465 \text{ V} \times 100 \text{ MHz} \times 4 = 6.9 \text{ mA} \quad (10)$$

注

For dimensioning the power supply, consider the total power consumption. The total power consumption is the sum of device power consumption and the power consumption of the load.

9.3.2 Thermal Management

For reliability and performance reasons, limit the die temperature to a maximum of 125°C. That is, as an estimate, T_A (ambient temperature) plus device power consumption times $R_{\theta JA}$ should not exceed 125°C.

Assuming the conditions in the [Power Dissipation Calculations](#) section and operating at an ambient temperature of 70°C with all outputs loaded, [公式 11](#) shows the estimate of the LMK00804B-Q1 junction temperature:

$$T_J = T_A + P_{Total} \times R_{\theta JA} = 70^\circ\text{C} + (124 \text{ mW} \times 48^\circ\text{C/W}) = 70^\circ\text{C} + 6.0^\circ\text{C} = 76.0^\circ\text{C} \quad (11)$$

Here are some recommendations to improve heat flow away from the die:

- Use multi-layer boards
- Specify a higher copper thickness for the board
- Increase the number of vias from the top level ground plane under and around the device to internal layers and to the bottom layer with as much copper area flow on each level as possible
- Apply air flow
- Leave unused outputs floating

Do's and Don'ts (接下页)

9.3.3 Recommendations for Unused Input and Output Pins

- **CLK_SEL and CLK_EN:** CLK_EN must be held low until a valid reference clock is provided before the engineer can use the pin to enable the outputs. These inputs both have an internal pullup (PU) according to 表 1. 表 1 shows the default floating state of these inputs:

表 1. Input Floating Default States

INPUT	FLOATING STATE SELECTION
CLK_SEL	CLK_P/CLK_N selected
CLK_EN	Synchronous outputs enable

- **CLK_P/CLK_N Inputs:** See 图 12 for the internal connections. When using a single-ended input, take note of the internal pullup and pulldown to make sure the unused input is properly biased. To interface a single-ended input to the CLK_P/CLK_N input, the configuration shown in 图 14 is recommended.
- **LVC MOS_CLK Input:** See 图 12 for the internal connection. The internal pulldown (PD) resistor ensures a low state when this input is left floating.
- **Outputs:** Any unused output may be left floating.

9.3.4 Input Slew Rate Considerations

LMK00804B-Q1 employs high-speed and low-latency circuit topology to allow ultra-low additive jitter/phase noise and high-frequency operation. To take advantage of these benefits in the system application, it is optimal for the input signal to have a high slew rate of 3 V/ns or greater. Driving the input with a slower slew rate can degrade the additive jitter and noise floor performance. For this reason, a differential signal input is recommended over a single-ended signal, because a differential signal typically provides a higher slew rate and common-mode-rejection.

10 Power Supply Recommendations

10.1 Power Supply Considerations

While there is no strict power supply sequencing requirement, it is generally best practice to sequence the supply input voltage (V_{DD}) before the supply output voltage (V_{DDO}).

10.1.1 Power-Supply Filtering

High-performance clock buffers are sensitive to noise on the power supply, which can dramatically increase the additive jitter of the buffer. Thus, it is essential to reduce noise from the system power supply, especially when jitter or phase noise is critical to applications.

The use of bypass capacitors eliminates the low-frequency noise from power supply, because they can provide a very low-impedance path for high-frequency noise and guard the power-supply system against induced fluctuations. The bypass capacitors also provide instantaneous current surges as required by the device, and should have low ESR. To use the bypass capacitors properly, place them close to the power supply terminals and lay out traces with short loops to minimize inductance. TI recommends that the engineer add as many high-frequency (for example, 0.1- μF) bypass capacitors as there are supply terminals in the package. TI recommends that the engineer insert a ferrite bead between the board power supply and the chip power supply to isolate the high-frequency switching noises generated by the clock driver. This would prevent leakage into the board supply. It is important to choose an appropriate ferrite bead with low DC resistance, because the bead must provide adequate isolation between the board supply and the chip supply. It is also important to maintain a voltage at the supply terminals that is greater than the minimum voltage required for proper operation.

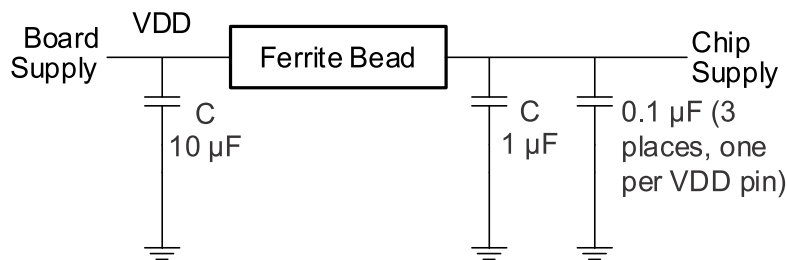


图 15. Power-Supply Decoupling

11 Layout

11.1 Layout Guidelines

11.1.1 Ground Planes

Solid ground planes are recommended because these planes provide a low-impedance return paths between the device and bypass capacitors, along with the clock source and destination devices.

LMK00804B-Q1 has a die attach pad (DAP) for enhanced thermal and electrical performance. Use five VIAs to connect the DAP to a solid GND plane. Full-through VIAs are preferred.

Avoid return paths of other system circuitry (for example, high-speed/digital logic, switching power supplies, and so forth) from passing through the local ground of the device to minimize noise coupling. Remember that noise coupling can lead to added jitter and spurious noise.

11.1.2 Power Supply Pins

Follow the power supply schematic and layout example described in [Power-Supply Filtering](#).

Layout Guidelines (接下页)

11.1.3 Differential Input Termination

- Place input termination or biasing resistors as close to the CLK_P/CLK_N pins as possible.
- Avoid or minimize vias in the 50-Ω input traces to minimize impedance discontinuities. Intra-pair skew should also be minimized on the differential input traces.
- If not used, CLK_P/CLK_N inputs may be left as no connect.

11.1.4 LVCMOS Input Termination

- Input termination is not necessary when the LVCMOS_CLK input is driven from a LVCMOS driver that is series-terminated to match the characteristic impedance of the trace. Otherwise, place the input termination resistor as close to the LVCMOS_CLK input as possible.
- Avoid or minimize vias in the 50-Ω input trace to minimize impedance discontinuities.
- If not used, LVCMOS_CLK input may be left as no connect.

11.1.5 Output Termination

- Place 43-Ω series termination resistors close to the Qx outputs at the launch of the 50-Ω traces.
- Avoid or minimize vias in the 50-Ω input traces to minimize impedance discontinuities.
- If not used, any Qx output should be left as no connect.

11.2 Layout Example

图 16 shows the recommended PCB design for good electrical and thermal performance. To maximize the heat dissipation from the package, a thermal landing pattern including multiple vias to a ground plane must be incorporated into the PCB within the footprint of the package. The thermal pad must be soldered down to ensure adequate heat conduction to of the package. Refer to the *Example Board Layout* in the *Package Option Addendum*.

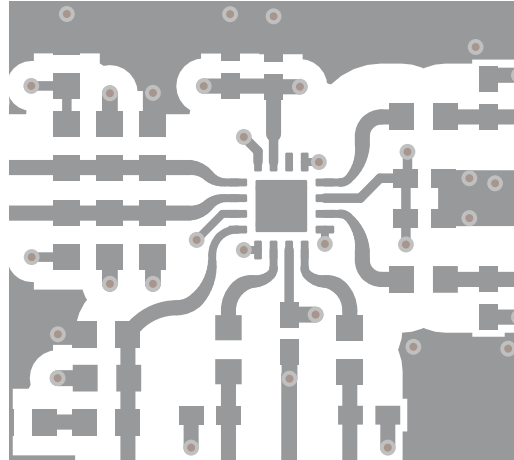


图 16. General PCB Ground Layout for Thermal Reliability

12 器件和文档支持

12.1 文档支持

12.1.1 相关文档

请参阅如下相关文档:

《[高速布局指南](#)》 (SCAA082)

12.2 接收文档更新通知

要接收文档更新通知, 请导航至 [TI.com.cn](#) 上的器件产品文件夹。单击右上角的 [通知我](#) 进行注册, 即可每周接收产品信息更改摘要。有关更改的详细信息, 请查看任何已修订文档中包含的修订历史记录。

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Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

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ESD 的损坏小至导致微小的性能降级, 大至整个器件故障。精密的集成电路可能更容易受到损坏, 这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

12.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更, 恕不另行通知, 且不会对此文档进行修订。如需获取此数据表的浏览器版本, 请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMK00804BQWRGTRQ1	ACTIVE	VQFN	RGT	16	3000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	804BQ	Samples
LMK00804BQWRGTTQ1	ACTIVE	VQFN	RGT	16	250	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	804BQ	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBsolete: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMK00804BQWRGTRQ1	VQFN	RGT	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
LMK00804BQWRGTTQ1	VQFN	RGT	16	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LMK00804BQWRGTRQ1	VQFN	RGT	16	3000	346.0	346.0	33.0
LMK00804BQWRGTTQ1	VQFN	RGT	16	250	210.0	185.0	35.0

RGT 16

GENERIC PACKAGE VIEW

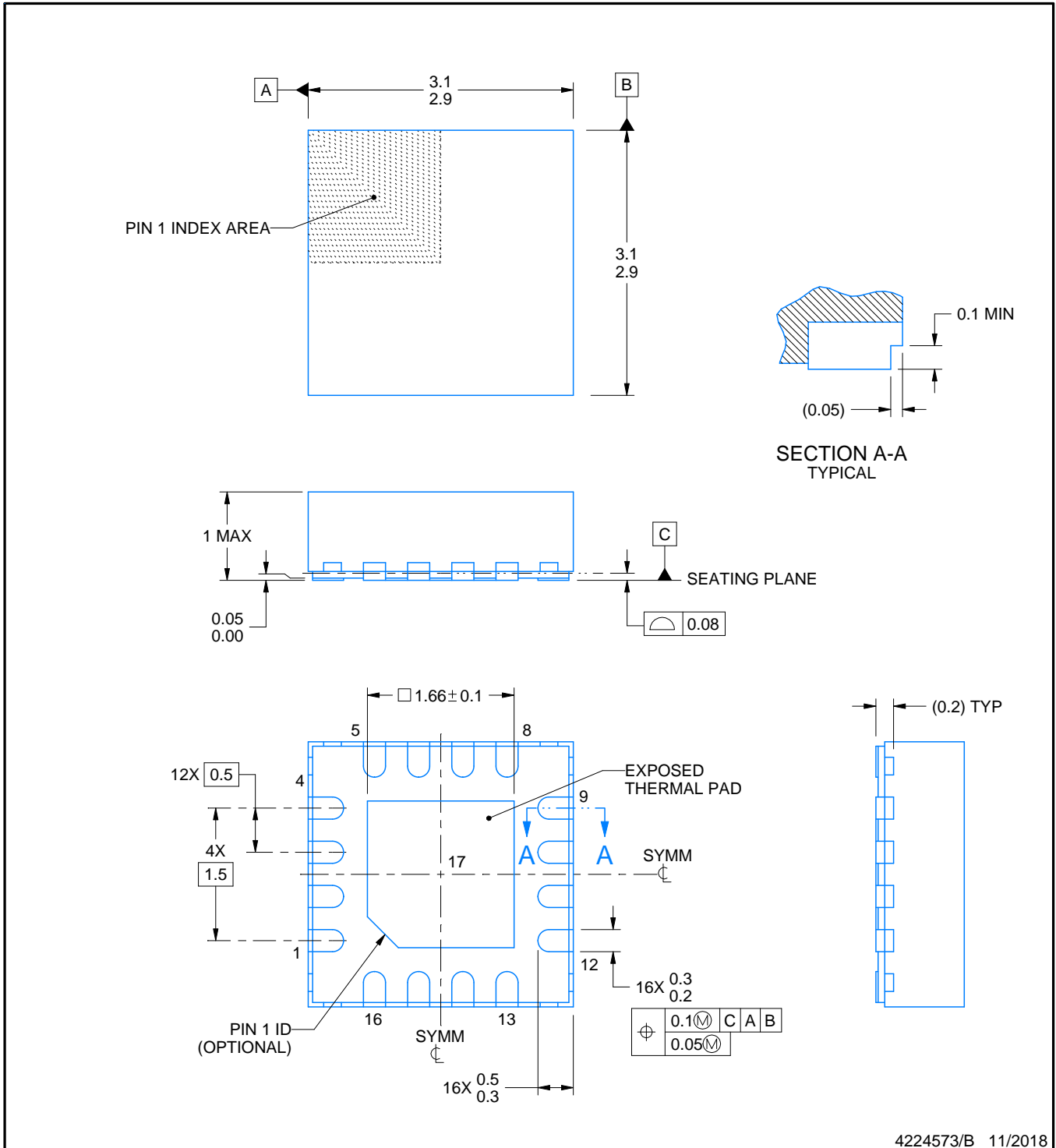
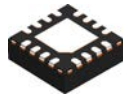
VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4203495/1



4224573/B 11/2018

NOTES:

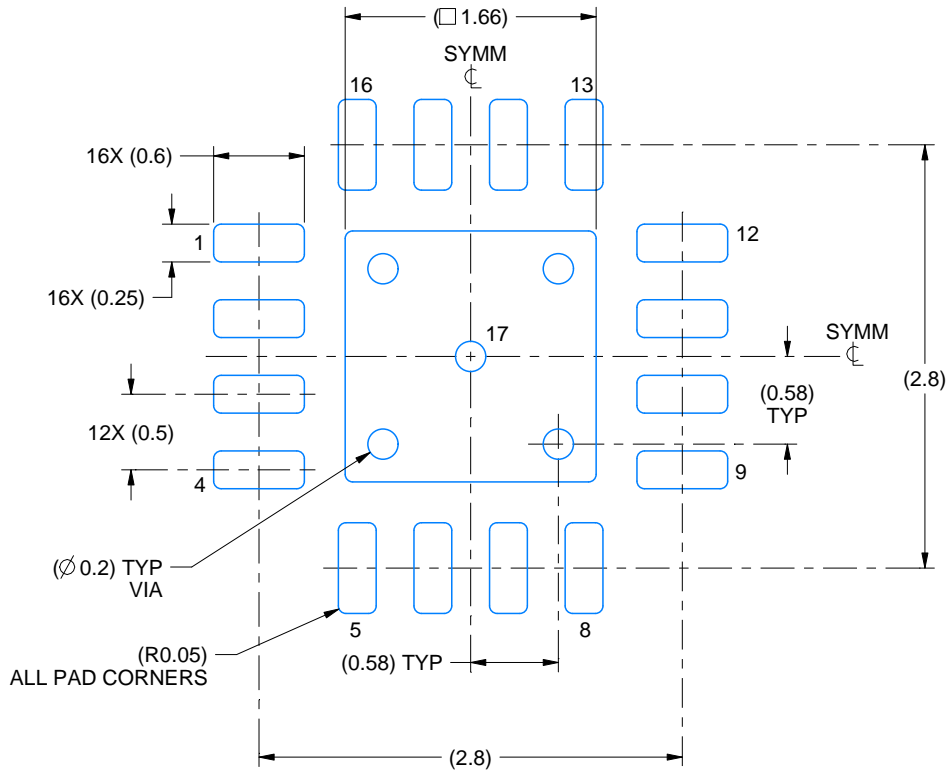
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

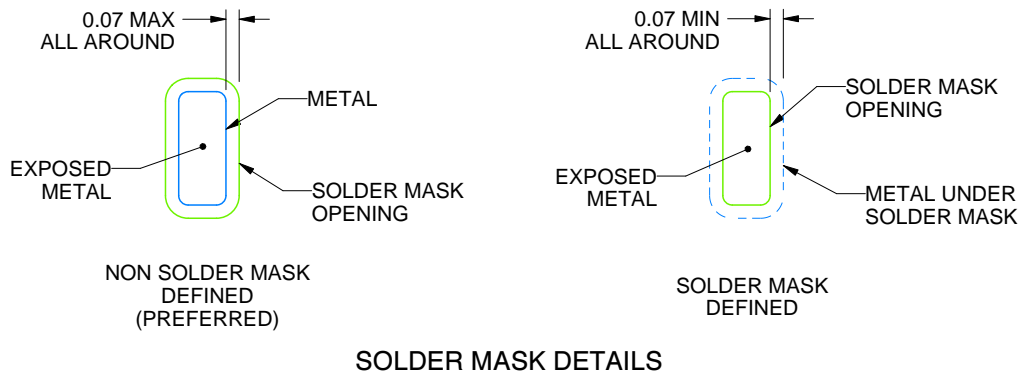
RGT0016J

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:20X



SOLDER MASK DETAILS

4224573/B 11/2018

NOTES: (continued)

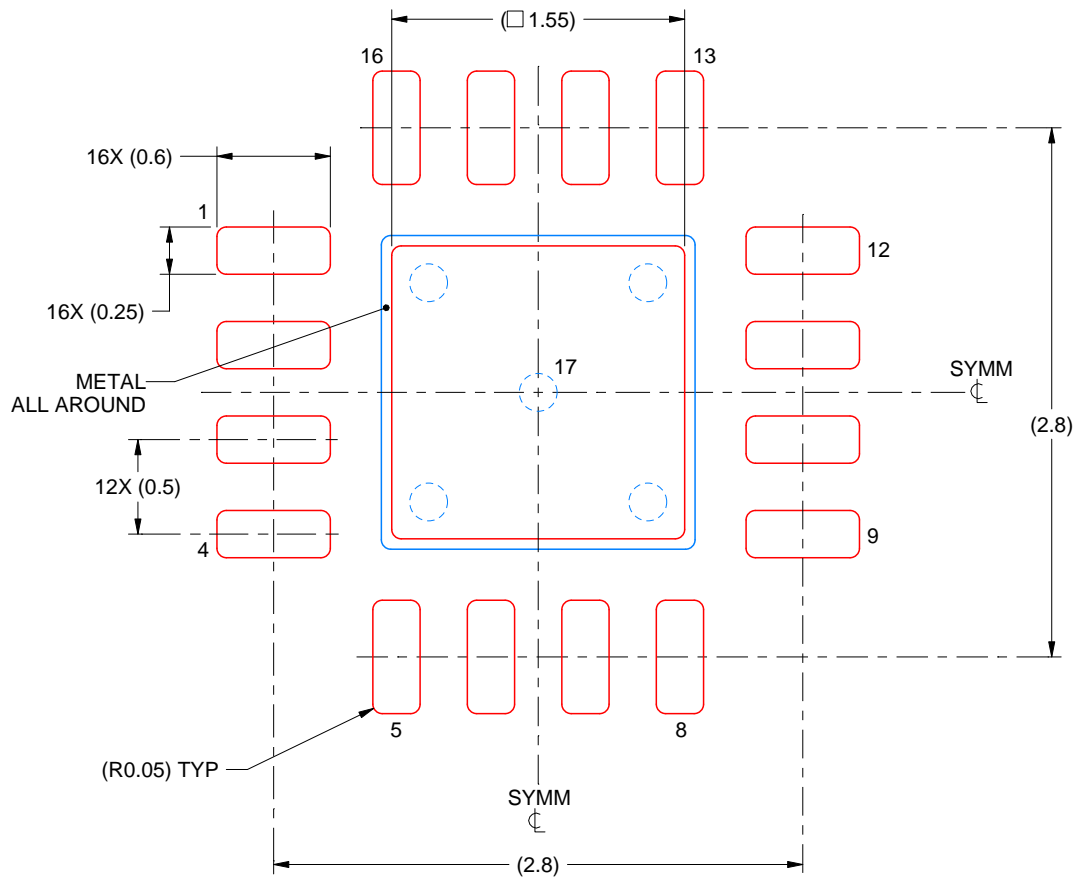
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

RGT0016J

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL

THERMAL PAD 17:
87% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:25X

4224573/B 11/2018

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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